

650V/5A Silicon Carbide Power Schottky Barrier Diode

Features

- Rated to 650V at 5 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

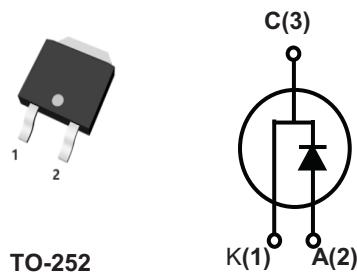
| Key Characteristics | | |
|-----------------------------|------------|-----------|
| V_{RRM} | 650 | V |
| $I_F, T_c \leq 160^\circ C$ | 5 | A |
| Q_c | 22 | nC |

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



| Part No. | Package Type | Marking |
|------------|--------------|---------|
| SC3S06505C | TO-252 | SC06505 |

Maximum Ratings

| Parameter | Symbol | Test Condition | Value | Unit |
|---|-----------|---|------------------|--------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 650 | V |
| Surge Peak Reverse Voltage | V_{RSM} | | 650 | V |
| DC Blocking Voltage | V_{DC} | | 650 | |
| Continuous Forward Current | I_F | $T_c=25^\circ C$ $T_c=135^\circ C$ | 21.4 9.9 | A |
| Repetitive Peak Forward Surge Current | I_{FRM} | $T_c=25^\circ C$, tp=10ms, Half Sine Wave, D=0.3 | 30 | A |
| Non-repetitive Peak Forward Surge Current | I_{FSM} | $T_c=25^\circ C$, tp=10ms, Half Sine Wave | 66 | A |
| Power Dissipation | P_{TOT} | $T_c=25^\circ C$ $T_c=110^\circ C$ | 82 35 | W |
| Operating Junction | T_j | | -55 °C to 175 °C | °C |
| Storage Temperature | T_{stg} | | -55 °C to 175 °C | °C |
| Mounting Torque | | M3 Screw 6-32 Screw | 1 8.8 | Nm lbf-in |

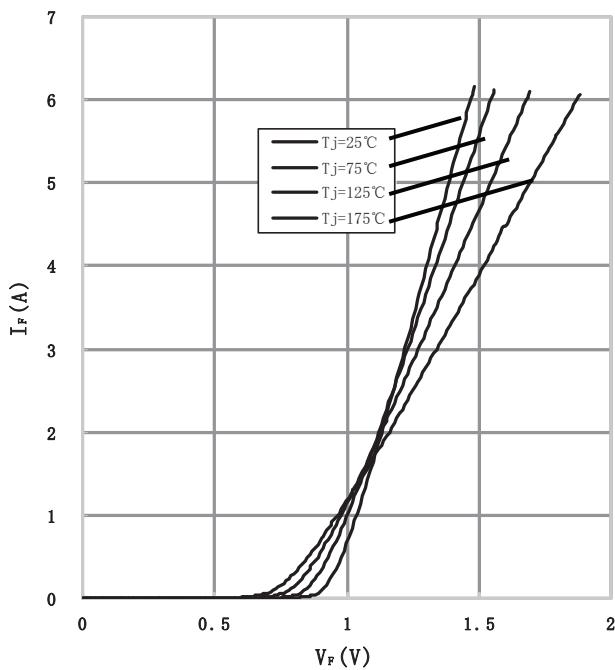
Thermal Characteristics

| Parameter | Symbol | Test Condition | Value | Unit |
|--|--------------|----------------|-------|------|
| | | | Typ. | |
| Thermal resistance from junction to case | $R_{th\ JC}$ | | 1.84 | °C/W |

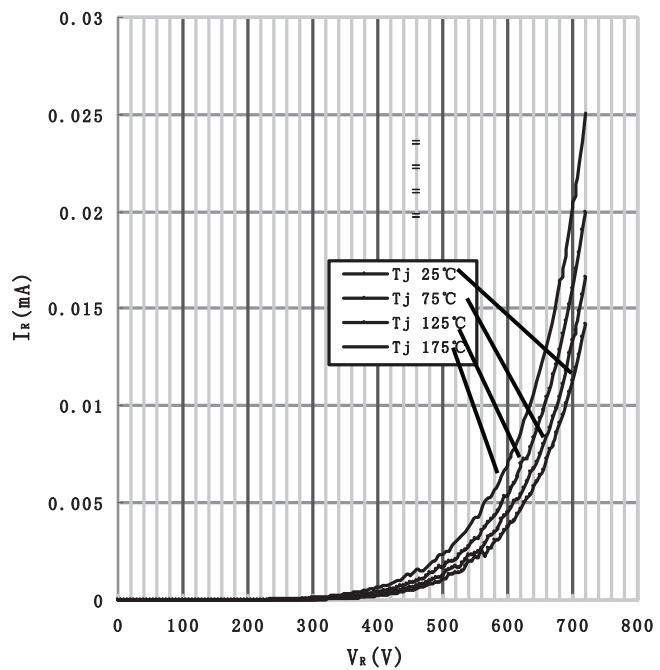
Electrical Characteristics

| Parameter | Symbol | Test Conditions | Numerical | | Unit |
|-------------------------|--------|--|-----------|------|---------|
| | | | Typ. | Max. | |
| Forward Voltage | V_F | $I_F=6A, T_j=25^\circ C$ | 1.36 | 1.7 | V |
| | | $I_F=6A, T_j=175^\circ C$ | 1.64 | 2 | |
| Reverse Current | I_R | $V_R=650V, T_j=25^\circ C$ | 0.12 | 50 | μA |
| | | $V_R=650V, T_j=175^\circ C$ | 0.91 | 100 | |
| Total Capacitive Charge | Q_C | $V_R=400V, T_j=25^\circ C$ $Q_C = \int_0^{V_R} C(V) dV$ | 22 | - | nC |
| Total Capacitance | C | $V_R=0V, T_j=25^\circ C, f=1MHz$ | 440 | - | pF |
| | | $V_R=200V, T_j=25^\circ C, f=1MHz$ | 42 | - | |
| | | $V_R=400V, T_j=25^\circ C, f=1MHz$ | 41 | - | |

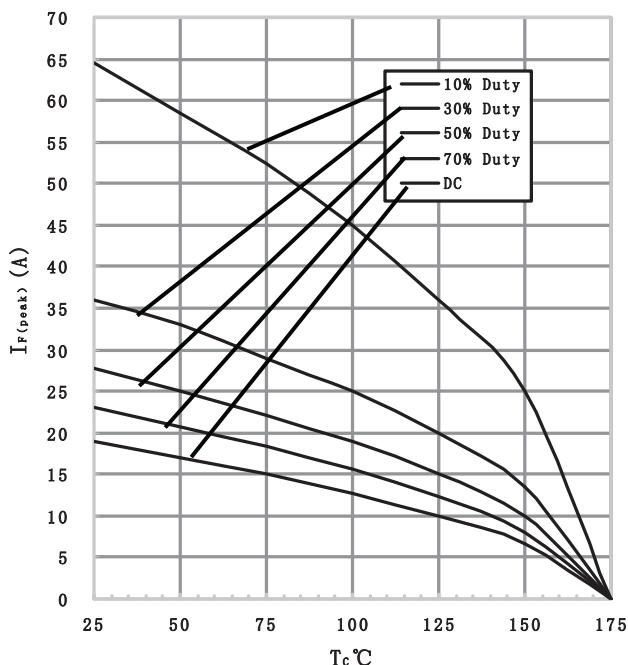
RATING AND CHARACTERISTICS CURVES (SC3S06505C)



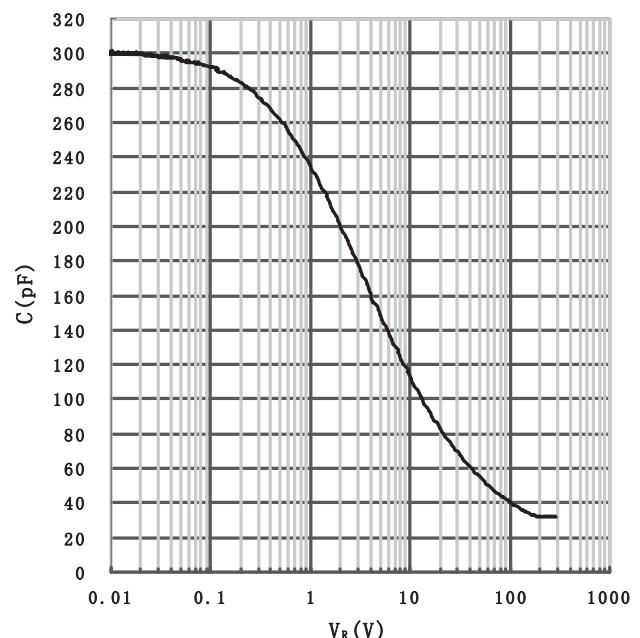
1) Forward IV characteristics as a function of T_j :



2) Reverse IV characteristics as a function of T_j :

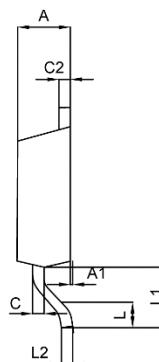
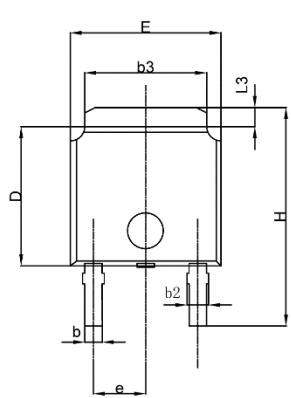


3) Current Derating



4) Capacitance vs. reverse voltage :

Package TO-252



| Symbol | DIMENSIONAL REQMTS | | |
|--------|--------------------|-------|-------|
| | Min | Nom | Max |
| E | 6.35 | 6.60 | 6.73 |
| L | 1.40 | 1.52 | 1.78 |
| L1 | 2.743REF | | |
| L2 | 0.508BSC | | |
| L3 | 0.89 | — | 1.27 |
| D | 5.97 | 6.10 | 6.22 |
| H | 9.40 | 10.00 | 10.40 |
| b | 0.64 | 0.76 | 0.89 |
| b2 | 0.76 | 0.84 | 1.14 |
| b3 | 4.95 | 5.34 | 5.46 |
| e | 2.286BSC | | |
| A | 2.18 | 2.30 | 2.39 |
| A1 | 0.00 | — | 0.13 |
| c | 0.46 | 0.50 | 0.61 |
| c2 | 0.46 | 0.50 | 0.60 |
| D1 | 5.21 | — | — |
| E1 | 4.32 | — | — |

Note:

1. All Dimension Are In mm